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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, LINbus, SPI, UART/USART, USB, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	50
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D - 16bit; D/A - 12bit
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl46z128vlh4

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Ratings 1

Thermal handling ratings 1.1

Table 1. Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T _{STG}	Storage temperature	-55	150	°C	1
T _{SDR}	Solder temperature, lead-free	_	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, High Temperature Storage Life.

2. Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

Moisture handling ratings 1.2

Table 2. Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level		3		1

1. Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

1.3 ESD handling ratings

Table 3. ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V _{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V _{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I _{LAT}	Latch-up current at ambient temperature of 105 °C	-100	+100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM).

2. Determined according to JEDEC Standard JESD22-C101, Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components.

Determined according to JEDEC Standard JESD78, IC Latch-Up Test.





1.4 Voltage and current operating ratings

Table 4. Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V _{DD}	Digital supply voltage	-0.3	3.8	V
I _{DD}	Digital supply current	_	120	mA
V _{IO}	IO pin input voltage	-0.3	V _{DD} + 0.3	V
Ι _D	Instantaneous maximum current single pin limit (applies to all port pins)	-25	25	mA
V _{DDA}	Analog supply voltage	V _{DD} – 0.3	V _{DD} + 0.3	V
V _{USB_DP}	USB_DP input voltage	-0.3	3.63	V
V _{USB_DM}	USB_DM input voltage	-0.3	3.63	V
V _{REGIN}	USB regulator input	-0.3	6.0	V

2 General

2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.



The midpoint is V_{IL} + (V_{IH} - V_{IL}) / 2

Figure 2. Input signal measurement reference

All digital I/O switching characteristics, unless otherwise specified, assume the output pins have the following characteristics.

- C_L=30 pF loads
- Slew rate disabled
- Normal drive strength



2.2 Nonswitching electrical specifications

2.2.1 Voltage and current operating requirements Table 5. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V _{DD}	Supply voltage	1.71	3.6	V	
V _{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	V _{DD} -to-V _{DDA} differential voltage	-0.1	0.1	V	
$V_{SS} - V_{SSA}$	V _{SS} -to-V _{SSA} differential voltage	-0.1	0.1	V	
V _{IH}	Input high voltage				
	• 2.7 V \leq V _{DD} \leq 3.6 V	$0.7 \times V_{DD}$	—	V	
	• $1.7 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$	$0.75 \times V_{DD}$	_	V	
VIL	Input low voltage				
	• 2.7 V \leq V _{DD} \leq 3.6 V	_	$0.35 \times V_{DD}$	V	
	• $1.7 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$	_	$0.3 \times V_{DD}$	V	
V _{HYS}	Input hysteresis	$0.06 \times V_{DD}$	_	V	
I _{ICIO}	IO pin negative DC injection current — single pin • V _{IN} < V _{SS} -0.3V	-3	_	mA	1
I _{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents of 16 contiguous pins • Negative current injection	-25	_	mA	
V _{ODPU}	Open drain pullup voltage level	V _{DD}	V _{DD}	V	2
V _{RAM}	V _{DD} voltage required to retain RAM	1.2	_	V	

- All I/O pins are internally clamped to V_{SS} through a ESD protection diode. There is no diode connection to V_{DD}. If V_{IN} greater than V_{IO_MIN} (= V_{SS}-0.3 V) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as R = (V_{IO_MIN} V_{IN})/II_{ICIO}I.
- 2. Open drain outputs must be pulled to V_{DD} .

2.2.2 LVD and POR operating requirements

Table 6. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{POR}	Falling V _{DD} POR detect voltage	0.8	1.1	1.5	V	—



Symbol	Description	Min.	Max.	Unit	Notes
V _{OL}	Output low voltage — Normal drive pad				1
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OL} = 5 mA	_	0.5	V	
	• 1.71 V \leq V _{DD} \leq 2.7 V, I _{OL} = 2.5 mA	_	0.5	v	
V _{OL}	Output low voltage — High drive pad				1
	• 2.7 V \leq V_{DD} \leq 3.6 V, I_{OL} = 20 mA	_	0.5	V	
	• $1.71 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}, \text{ I}_{\text{OL}} = 10 \text{ mA}$	_	0.5	V	
I _{OLT}	Output low current total for all ports	—	100	mA	
I _{IN}	Input leakage current (per pin) for full temperature range	_	1	μA	3
I _{IN}	Input leakage current (per pin) at 25 °C	—	0.025	μA	3
I _{IN}	Input leakage current (total all pins) for full temperature range	_		μA	3
I _{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μΑ	
R _{PU}	Internal pullup resistors	20	50	kΩ	4

Table 7. Voltage and current operating behaviors (continued)

1. PTB0, PTB1, PTD6, and PTD7 I/O have both high drive and normal drive capability selected by the associated PTx_PCRn[DSE] control bit. All other GPIOs are normal drive only.

- 2. The reset pin only contains an active pull down device when configured as the RESET signal or as a GPIO. When configured as a GPIO output, it acts as a pseudo open drain output.
- 3. Measured at $V_{DD} = 3.6 V$

4. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}

2.2.4 Power mode transition operating behaviors

All specifications except t_{POR} and VLLSx \rightarrow RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 48 MHz
- Bus and flash clock = 24 MHz
- FEI clock mode

POR and VLLSx \rightarrow RUN recovery use FEI clock mode at the default CPU and system frequency of 21 MHz, and a bus and flash clock frequency of 10.5 MHz.

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.8 V to execution of the first instruction across the operating temperature range of the chip.			300	μs	1

 Table 8. Power mode transition operating behaviors



Symbol	Description			٦	empera	ature (°	C)		Unit
			-40	25	50	70	85	105	
I _{IREFSTEN4MHz}	4 MHz internal reference clock Measured by entering STOP o with 4 MHz IRC enabled.	(IRC) adder. r VLPS mode	56	56	56	56	56	56	μA
I _{IREFSTEN32KHz}	32 kHz internal reference clock Measured by entering STOP n 32 kHz IRC enabled.	(IRC) adder. node with the	52	52	52	52	52	52	μA
I _{EREFSTEN4MHz}	External 4 MHz crystal clock a Measured by entering STOP o with the crystal enabled.	dder. r VLPS mode	206	228	237	245	251	258	μA
I _{EREFSTEN32KHz}	External 32 kHz crystal clock	VLLS1	440	490	540	560	570	580	nA
	adder by means of the	VLLS3	440	490	540	560	570	580]
	EREFSTEN] bits. Measured	LLS	490	490	540	560	570	680	
	by entering all modes with the crystal enabled.	VLPS	510	560	560	560	610	680	
	crystal enabled.	STOP	510	560	560	560	610	680]
I _{CMP}	CMP peripheral adder measure the device in VLLS1 mode with using the 6-bit DAC and a sing input for compare. Includes 6-b consumption.	ed by placing n CMP enabled le external pit DAC power	22	22	22	22	22	22	μA
I _{RTC}	RTC peripheral adder measure the device in VLLS1 mode with kHz crystal enabled by means RTC_CR[OSCE] bit and the R for 1 minute. Includes ERCLK3 external crystal) power consum	ed by placing n external 32 of the TC ALARM set 32K (32 kHz nption.	432	357	388	475	532	810	nA
I _{UART}	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at	MCGIRCLK (4 MHz internal reference clock)	66	66	66	66	66	66	μA
	115200 baud rate. Includes selected clock source power consumption.	OSCERCLK (4 MHz external crystal)	214	237	246	254	260	268	
I _{TPM}	TPM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output	MCGIRCLK (4 MHz internal reference clock)	86	86	86	86	86	86	μA
	compare generating 100 Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents.	OSCERCLK (4 MHz external crystal)	235	256	265	274	280	287	

Table 10. Low power mode peripheral adders — typical value



Symbol	Description		Т	empera	ature (°	C)		Unit
		-40	25	50	70	85	105	
I _{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	μA
I _{ADC}	ADC peripheral adder combining the measured values at V_{DD} and V_{DDA} by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	366	366	366	366	366	366	μA
I _{LCD}	LCD peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the OSC0_CR[EREFSTEN, EREFSTEN] bits. VIREG disabled, resistor bias network enabled, 1/8 duty cycle, 8 x 36 configuration for driving 288 Segments, 32 Hz frame rate, no LCD glass connected. Includes ERCLK32K (32 kHz external crystal) power consumption.	5	5	5	5	5	5	μA

 Table 10. Low power mode peripheral adders — typical value (continued)

2.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE for run mode, and BLPE for VLPR mode
- USB regulator disabled
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA



Peripheral operating requirements and behaviors

3.4.1.3 Flash high voltage current behaviors Table 23. Flash high voltage current behaviors

Symbol	Description	Min.	Тур.	Max.	Unit
I _{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I _{DD_ERS}	Average current adder during high voltage flash erase operation		1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 24. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes		
Program Flash								
t _{nvmretp10k}	Data retention after up to 10 K cycles	5	50	—	years	—		
t _{nvmretp1k}	Data retention after up to 1 K cycles	20	100	_	years	_		
n _{nvmcycp}	Cycling endurance	10 K	50 K		cycles	2		

 Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.

2. Cycling endurance represents number of program/erase cycles at -40 °C \leq T_j \leq 125 °C.

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in Table 25 and Table 26 are achievable on the differential pins ADCx_DP0, ADCx_DM0.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.



Symbol	Description	Min.	Тур.	Max.	Unit
V _{DD}	Supply voltage	1.71		3.6	V
I _{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	_	—	200	μA
I _{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	_	20	μA
V _{AIN}	Analog input voltage	$V_{SS} - 0.3$	_	V _{DD}	V
V _{AIO}	Analog input offset voltage	—	_	20	mV
V _H	Analog comparator hysteresis ¹				
	• CR0[HYSTCTR] = 00	—	5	_	mV
	 CR0[HYSTCTR] = 01 	—	10	_	mV
	 CR0[HYSTCTR] = 10 	—	20	_	mV
	 CR0[HYSTCTR] = 11 	—	30		mV
V _{CMPOh}	Output high	V _{DD} – 0.5	_	—	V
V _{CMPOI}	Output low	—	_	0.5	V
t _{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t _{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay ²	_	_	40	μs
I _{DAC6b}	6-bit DAC current adder (enabled)	_	7	—	μA
INL	6-bit DAC integral non-linearity	-0.5	—	0.5	LSB ³
DNL	6-bit DAC differential non-linearity	-0.3		0.3	LSB

3.6.2 CMP and 6-bit DAC electrical specifications Table 27. Comparator and 6-bit DAC electrical specifications

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD} -0.6 V.

 Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.

3. 1 LSB = $V_{reference}/64$



Figure 11. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

3.6.3 12-bit DAC electrical characteristics

3.6.3.1 12-bit DAC operating requirements Table 28. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V _{DDA}	Supply voltage	1.71	3.6	V	
V _{DACR}	Reference voltage	1.13	3.6	V	1
CL	Output load capacitance	—	100	pF	2
١L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or $V_{\text{REFH}}.$

2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.



Peripheral operating requirements and behaviors

3.6.3.2 12-bit DAC operating behaviors Table 29. 12-bit DAC operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DDA_DACL}	Supply current — low-power mode	_	—	250	μA	
I _{DDA_DACH}	Supply current — high-speed mode	_	—	900	μA	
t _{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	_	100	200	μs	1
t _{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	_	15	30	μs	1
t _{CCDACLP}	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	_	0.7	1	μs	1
V _{dacoutl}	DAC output voltage range low — high- speed mode, no load, DAC set to 0x000	_	—	100	mV	
V _{dacouth}	DAC output voltage range high — high- speed mode, no load, DAC set to 0xFFF	V _{DACR} -100	_	V _{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	_	±8	LSB	2
DNL	Differential non-linearity error — $V_{DACR} > 2$ V	_	_	±1	LSB	3
DNL	Differential non-linearity error — V _{DACR} = VREF_OUT	_	_	±1	LSB	4
VOFFSET	Offset error	_	±0.4	±0.8	%FSR	5
E _G	Gain error	_	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \ge 2.4 V$	60	—	90	dB	
T _{CO}	Temperature coefficient offset voltage	_	3.7	_	μV/C	6
T _{GE}	Temperature coefficient gain error	_	0.000421		%FSR/C	
Rop	Output resistance (load = $3 \text{ k}\Omega$)	_	—	250	Ω	
SR	Slew rate -80h \rightarrow F7Fh \rightarrow 80h				V/µs	
	 High power (SP_{HP}) 	1.2	1.7	—		
	• Low power (SP _{LP})	0.05	0.12	—		
BW	3dB bandwidth				kHz	
	 High power (SP_{HP}) 	550	_	—		
	 Low power (SP_{LP}) 	40	_	—		

1. Settling within ±1 LSB

2. The INL is measured for 0 + 100 mV to V_{DACR} –100 mV

3. The DNL is measured for 0 + 100 mV to V_{DACR} –100 mV

4. The DNL is measured for 0 + 100 mV to V_{DACR} –100 mV with V_{DDA} > 2.4 V

5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} - 100 mV

V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_CO:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

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Peripheral operating requirements and behaviors

3.8.3 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

All timing is shown with respect to 20% V_{DD} and 80% V_{DD} thresholds, unless noted, as well as input signal transitions of 3 ns and a 30 pF maximum load on all SPI pins.

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f _{op}	Frequency of operation	f _{periph} /2048	f _{periph} /2	Hz	1
2	t _{SPSCK}	SPSCK period	2 x t _{periph}	2048 x	ns	2
				t _{periph}		
3	t _{Lead}	Enable lead time	1/2	—	t _{SPSCK}	
4	t _{Lag}	Enable lag time	1/2		t _{SPSCK}	
5	t _{WSPSCK}	Clock (SPSCK) high or low time	t _{periph} - 30	1024 x	ns	—
				t _{periph}		
6	t _{SU}	Data setup time (inputs)	18	_	ns	—
7	t _{HI}	Data hold time (inputs)	0	_	ns	—
8	t _v	Data valid (after SPSCK edge)	—	15	ns	—
9	t _{HO}	Data hold time (outputs)	0	_	ns	—
10	t _{RI}	Rise time input	—	t _{periph} - 25	ns	—
	t _{FI}	Fall time input	1			
11	t _{RO}	Rise time output	—	25	ns	_
	t _{FO}	Fall time output				

 Table 31. SPI master mode timing on slew rate disabled pads

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).

2. $t_{periph} = 1/f_{periph}$

 Table 32.
 SPI master mode timing on slew rate enabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f _{op}	Frequency of operation	f _{periph} /2048	f _{periph} /2	Hz	1
2	t _{SPSCK}	SPSCK period	2 x t _{periph}	2048 x	ns	2
				t _{periph}		
3	t _{Lead}	Enable lead time	1/2	_	t _{SPSCK}	_
4	t _{Lag}	Enable lag time	1/2		t _{SPSCK}	_
5	t _{WSPSCK}	Clock (SPSCK) high or low time	t _{periph} - 30	1024 x	ns	—
				t _{periph}		
6	t _{SU}	Data setup time (inputs)	96	—	ns	_
7	t _{HI}	Data hold time (inputs)	0	—	ns	—



Num.	Symbol	Description	Min.	Max.	Unit	Note
8	t _v	Data valid (after SPSCK edge)	—	52	ns	—
9	t _{HO}	Data hold time (outputs)	0	—	ns	—
10	t _{RI}	Rise time input	—	t _{periph} - 25	ns	
	t _{FI}	Fall time input				
11	t _{RO}	Rise time output	—	36	ns	—
	t _{FO}	Fall time output				

Table 32. SPI master mode timing on slew rate enabled pads (continued)

- 1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
- 2. $t_{periph} = 1/f_{periph}$



1. If configured as an output.

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 14. SPI master mode timing (CPHA = 0)



3.8.6.1 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK (as an input) pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15.5	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	_	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	19	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	26	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

Table 36. I2S/SAI master mode timing



Figure 19. I2S/SAI timing — master modes



121 BGA	100 LQFP	64 BGA	64 LQFP	Pin Name	Default	ALTO	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
D3	94	A4	58	PTD1	LCD_P41/ ADC0_SE5b	LCD_P41/ ADC0_SE5b	PTD1	SPI0_SCK		TPM0_CH1			LCD_P41
C3	95	C2	59	PTD2	LCD_P42	LCD_P42	PTD2	SPI0_MOSI	UART2_RX	TPM0_CH2	SPI0_MISO		LCD_P42
B3	96	B3	60	PTD3	LCD_P43	LCD_P43	PTD3	SPI0_MISO	UART2_TX	TPM0_CH3	SPI0_MOSI		LCD_P43
A3	97	A3	61	PTD4/ LLWU_P14	LCD_P44	LCD_P44	PTD4/ LLWU_P14	SPI1_PCS0	UART2_RX	TPM0_CH4			LCD_P44
A2	98	C1	62	PTD5	LCD_P45/ ADC0_SE6b	LCD_P45/ ADC0_SE6b	PTD5	SPI1_SCK	UART2_TX	TPM0_CH5			LCD_P45
B2	99	B2	63	PTD6/ LLWU_P15	LCD_P46/ ADC0_SE7b	LCD_P46/ ADC0_SE7b	PTD6/ LLWU_P15	SPI1_MOSI	UART0_RX		SPI1_MISO		LCD_P46
A1	100	A2	64	PTD7	LCD_P47	LCD_P47	PTD7	SPI1_MISO	UART0_TX		SPI1_MOSI		LCD_P47
J3	_	l	_	NC	NC	NC							
H3	_	_	_	NC	NC	NC							
K4	—	-	-	NC	NC	NC							
L7	_	_	_	NC	NC	NC							
J9	-	-	—	NC	NC	NC							
J4	—		—	NC	NC	NC							
H11	-	Ι	—	NC	NC	NC							
F11	-	-	—	NC	NC	NC							
A5	—	_	—	NC	NC	NC							
B5	_	-	_	NC	NC	NC							
A4	_	I	—	NC	NC	NC							
B1	—	_	—	NC	NC	NC							
C2	—	-	-	NC	NC	NC							
C1	-	-	_	NC	NC	NC							
D2	_	_	_	NC	NC	NC							
D1	-	_	_	NC	NC	NC							
E1	_	_	_	NC	NC	NC							

5.2 KL46 pinouts

The following figures show the pinout diagrams for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, ssee KL46 Signal Multiplexing and Pin Assignments.



	1	2	3	4	5	6	7	8	9	10	11	
A	PTD7	PTD5	PTD4/ LLWU_P14	NC	NC	PTC13	PTC8	PTC4/ LLWU_P8	VLL1	VLL2	VLL3	A
в	NC	PTD6/ LLWU_P15	PTD3	PTC18	NC	PTC12	PTC7	PTC3/ LLWU_P7	PTC0	PTB16	VCAP2	в
с	NC	NC	PTD2	PTC17	PTC11	PTC10	PTC6/ LLWU_P10	PTC2	PTB19	PTB11	VCAP1	с
D	NC	NC	PTD1	PTD0	PTC16	PTC9	PTC5/ LLWU_P9	PTC1/ LLWU_P6/ RTC_CLKIN	PTB18	PTB10	PTB8	D
E	NC	PTE2	PTE1	PTE0	VDD	VDD	VDD	PTB23	PTB17	PTB9	PTB7	E
F	USB0_DP	USB0_DM	PTE6	PTE3	VDDA	VSSA	VSS	PTB22	PTB21	PTB20	NC	F
G	VOUT33	VREGIN	VSS	PTE5	VREFH	VREFL	VSS	PTB3	PTB2	PTB1	PTB0/ LLWU_P5	G
н	PTE16	PTE17	NC	PTA7	PTE24	PTE26	PTE4	PTA1	PTA3	PTA17	NC	н
J	PTE18	PTE19	NC	NC	PTE25	PTA0	PTA2	PTA4	NC	PTA16	PTA20	J
к	PTE20	PTE21	PTA6	NC	PTE30	VDD	PTA5	PTA12	PTA14	VSS	PTA19	к
L	PTE22	PTE23	PTE29	PTE31	VSS	VSS	NC	PTA13	PTA15	VDD	PTA18	L
	1	2	3	4	5	6	7	8	9	10	11	I

Figure 23. KL46 121-pin BGA pinout diagram

NP





Figure 24. KL46 100-pin LQFP pinout diagram



6.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to **freescale.com** and perform a part number search for the following device numbers: PKL46 and MKL46

7 Part identification

7.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

7.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

7.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	 M = Fully qualified, general market flow P = Prequalification
KL##	Kinetis family	• KL46
A	Key attribute	• Z = Cortex-M0+
FFF	Program flash memory size	 128 = 128 KB 256 = 256 KB
R	Silicon revision	 (Blank) = Main A = Revision after main
Т	Temperature range (°C)	• V = -40 to 105
PP	Package identifier	 LH = 64 LQFP (10 mm x 10 mm) MP = 64 MAPBGA (5 mm x 5 mm)

Table 42. Part number fields descriptions



Terminology and guidelines

8.5 Result of exceeding a rating



8.6 Relationship between ratings and operating requirements



8.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.



Revision history



8.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

 Table 43.
 Typical value conditions

Symbol	Description	Value	Unit
T _A	Ambient temperature	25	۵°C
V _{DD}	3.3 V supply voltage	3.3	V

9 Revision history

The following table provides a revision history for this document.

Rev. No.	Date	Substantial Changes
3	3/2014	 Updated the front page and restructured the chapters Updated Voltage and current operating behaviors Updated EMC radiated emissions operating behaviors Updated Power mode transition operating behaviors

Table 44. Revision history





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